

30V Dual P-Channel MOSFET



SOP-8

Pin Definition:



1. Source 1 8. Drain 1 2. Gate 1 7. Drain 1 3. Source 2 6. Drain 2

4. Gate 2 5. Drain 2

PRODUCT SUMMARY

V _{DS} (V)	$R_{DS(on)}(m\Omega)$	I _D (A)	
-30	25 @ V _{GS} = -10V	-7.1	
	41 @ V _{GS} = -4.5V	-5.5	

Features

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

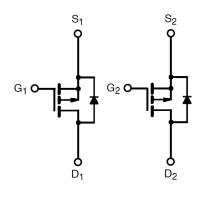
Application

- Load Switches
- Notebook PCs
- Desktop PCs

Ordering Information

Part No.	Package	Packing
TSM4925DCS RL	SOP-8	2.5Kpcs / 13" Reel

Block Diagram



Dual P-Channel MOSFET

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V_{DS}	-30	V	
Gate-Source Voltage		V_{GS}	±20	V	
Continuous Drain Current		I _D	-7.1	А	
Pulsed Drain Current		I _{DM}	-40	А	
Continuous Source Current (Diode Con	duction) ^{a,b}	I _S	-1.7	А	
Maximum Power Dissipation	Ta = 25°C	В	2.0	W	
	Ta = 75°C	P _D	1.3		
Operating Junction Temperature		TJ	+150	°C	
Operating Junction and Storage Temperature Range		T _J , T _{STG}	- 55 to +150	°C	

Thermal Performance

Parameter	Symbol	Limit	Unit
Junction to Case Thermal Resistance	R⊖ _{JC}	30	°C/W
Junction to Ambient Thermal Resistance (PCB mounted)	RO _{JA}	50	°C/W

Notes:

- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on FR4 Board, t ≤ 10 sec.



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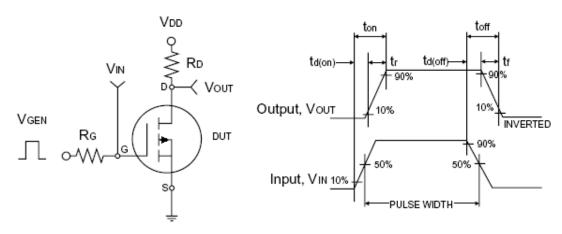


Electrical Specifications (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = -250uA$	BV _{DSS}	-30	1		V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	$V_{GS(TH)}$	-1	-	-3	V
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I _{GSS}		1	±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = -30V, V_{GS} = 0V$	I _{DSS}		1	-1.0	μA
On-State Drain Current ^a	$V_{DS} = -5V, V_{GS} = -10V$	I _{D(ON)}	-40	1		Α
Drain-Source On-State Resistance	$V_{GS} = -10V, I_D = -7.1A$	Ь		20	25	mΩ
Dialii-Source Oii-State Resistance	$V_{GS} = -4.5V, I_{D} = -5.5A$	$R_{DS(ON)}$		33	41	
Forward Transconductance ^a	$V_{DS} = -10V, I_{D} = -7.1A$	g _{fs}		24		S
Diode Forward Voltage	$I_S = -1.7A$, $V_{GS} = 0V$	V_{SD}		-0.8	-1.2	V
Dynamic ^b						
Total Gate Charge	$V_{DS} = -15V, I_{D} = -7.1A,$	Q_g		33	70	
Gate-Source Charge	$V_{DS} = -15V, I_D = -7.1A,$ $V_{GS} = -10V$	Q_gs		5.8		nC
Gate-Drain Charge	V _{GS} = -10V	Q_{gd}		8.6		
Input Capacitance	$V_{DS} = -15V, V_{GS} = 0V,$ f = 1.0MHz	C _{iss}		1573	1900	
Output Capacitance		C _{oss}		319		pF
Reverse Transfer Capacitance	1 - 1.0IVINZ	C _{rss}		211	295	
Switching ^c						
Turn-On Delay Time	$V_{DD} = -15V, R_{L} = 15\Omega,$ $I_{D} = -1A, V_{GEN} = -10V,$ $R_{G} = 6\Omega$	t _{d(on)}		10	15	
Turn-On Rise Time		t _r		15	25	nS
Turn-Off Delay Time		$t_{d(off)}$		110	170	110
Turn-Off Fall Time	11G - 022	t _f		70	110	

Notes:

- a. pulse test: PW ≤300µS, duty cycle ≤2%
- b. For DESIGN AID ONLY, not subject to production testing.
- b. Switching time is essentially independent of operating temperature.



Switching Test Circuit

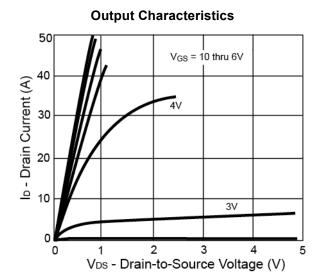
Switchin Waveforms



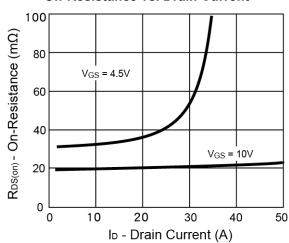
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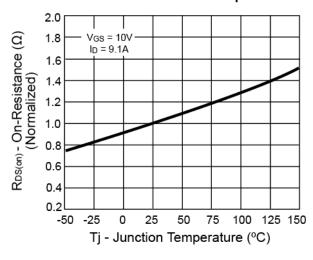
Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)



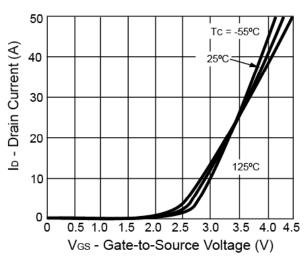
On-Resistance vs. Drain Current



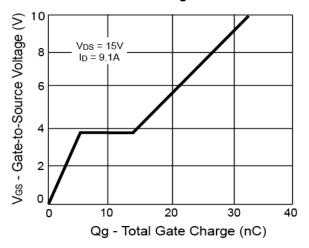
On-Resistance vs. Junction Temperature



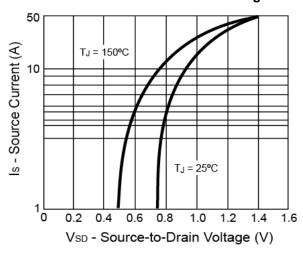
Transfer Characteristics



Gate Charge



Source-Drain Diode Forward Voltage



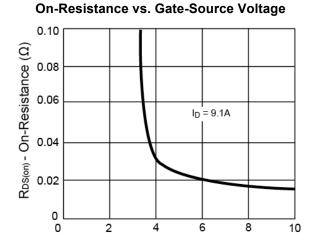


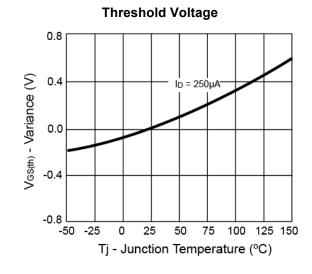


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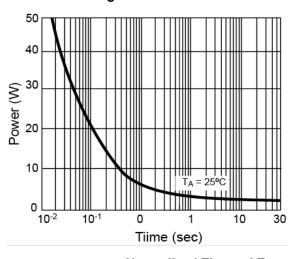
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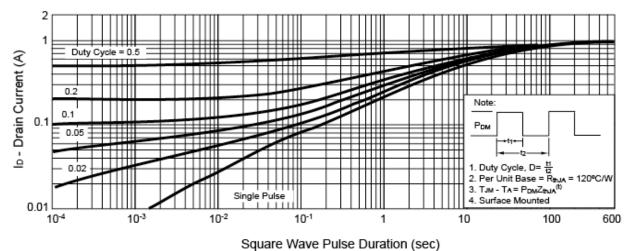




V_{GS} - Gate-to-Source Voltage (V)



Normalized Thermal Transient Impedance, Junction-to-Ambient

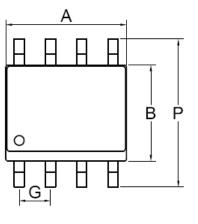


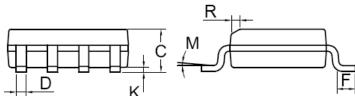


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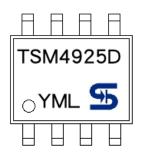
SOP-8 Mechanical Drawing





	SOP-8 DIMENSION					
DIM	MILLIMETERS		INCHES			
DIIVI	MIN	MAX	MIN	MAX.		
Α	4.80	5.00	0.189	0.196		
В	3.80	4.00	0.150	0.157		
С	1.35	1.75	0.054	0.068		
D	0.35	0.49	0.014	0.019		
F	0.40	1.25	0.016	0.049		
G	1.27	BSC	0.05	BSC		
K	0.10	0.25	0.004	0.009		
М	0°	7°	0°	7°		
Р	5.80	6.20	0.229	0.244		
R	0.25	0.50	0.010	0.019		

Marking Diagram



Y = Year CodeM = Month Code

(**A**=Jan, **B**=Feb, **C**=Mar, **D**=Apl, **E**=May, **F**=Jun, **G**=Jul, **H**=Aug, **I**=Sep, **J**=Oct, **K**=Nov, **L**=Dec)

L = Lot Code

5/6

Version: A07



TSM4925D 30V Dual P-Channel MOSFET

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